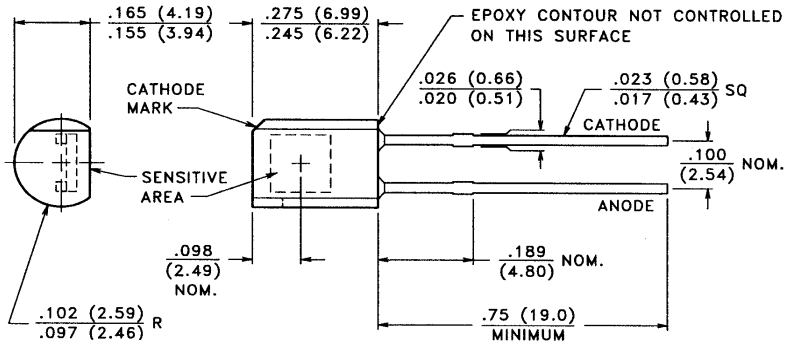
Alternate Source/ Second Source Photodiodes

VTD206KH

(SFH206K INDUSTRY EQUIVALENT)



PACKAGE DIMENSIONS inch (mm)



CASE 61 TO-92 TYPE (FLAT LENS)
CHIP ACTIVE AREA: .011 in^2 (7.41 mm^2)

PRODUCT DESCRIPTION

Large area planar silicon photodiode in a waterclear, cast epoxy sidelooker, similar in outline to the TO-92 package. These diodes exhibit low dark current under reverse bias and fast speed of response.

ABSOLUTE MAXIMUM RATINGS

Storage Temperature:	-40°C to 100°C
Operating Temperature:	-40°C to 100°C

ELECTRO-OPTICAL CHARACTERISTICS @ 25°C

SYMBOL	CHARACTERISTIC	TEST CONDITIONS	VTD206KH			UNITS
			Min.	Typ.	Max.	
I_{SC}	Short Circuit Current	1000 Lux, 2856 K	50	80		µA
TC I_{SC}	I_{SC} Temperature Coefficient	2856 K		.20		%/°C
V_{OC}	Open Circuit Voltage	940 nm, H = 0.5 mW/cm^2	310	365		mV
TC V_{OC}	V_{OC} Temperature Coefficient	2856 K		-2.6		mV/°C
I_D	Dark Current	H = 0, V_R = 10 V		2	30	nA
C_J	Junction Capacitance	H = 0, V_R = 0 V, 1 MHz		72		pF
t_R/t_F	Rise/Fall Time @ RL = 50Ω	V_R = 5 V, 850 nm		20		nsec
S_R	Sensitivity	@ Peak		0.6		A/W
λ_{range}	Spectral Application Range		400		1100	nm
λ_p	Spectral Response - Peak			925		nm
V_{BR}	Breakdown Voltage		20	50		V
$\theta_{1/2}$	Angular Resp.-50% Resp. Pt.			±60		Degrees

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